

## Specification of Photodiode

PD2501

[PIN-PD]

### 1) Commodity Type and Physical Characteristics.

1. Structure : Planer type PIN Photodiode
2. Electrode : Top Side Anode side : Aluminum Alloy  
Bottom Side Cathode side: Au Alloy
3. Electrode Pad : 130um\*960um Fig.1
4. Chip Size : 3.0mm\*1.25mm Fig.1
5. Active Area : 2.5mm\*1.0mm Fig.1
6. Chip Thickness : 0.30±0.04mm

### 2) Electro-Optical Characteristics (Ta=25°C)

| Item                      | Symbol      | Condition          | Minimum | Typical | Maximum | unit |
|---------------------------|-------------|--------------------|---------|---------|---------|------|
| Reverse Photo Current     | $I_L$       | $V_R=1V, L=1000Lx$ |         | 15      |         | uA   |
| Reverse Dark Current      | $I_D$       | $V_R=1V$           |         |         | 5       | nA   |
| Reverse Breakdown Voltage | $V_{(BR)R}$ | $I_R=10uA, L=0Lx$  |         | 150     |         | V    |
| Spectral Responsivity     | $S$         | $\lambda_P=940nm$  |         | 0.55    |         | A/W  |
| Total Capacitance         | $C_T$       | $V_R=1V, f=1MHz$   |         | 30      |         | pF   |
| Rise/Fall Time(10% ~ 90%) | $t_r$       | $R_L=1KW, V_R=1V$  |         | 30      |         | us   |
|                           | $t_f$       |                    |         | 30      |         | us   |

[Unit : um]

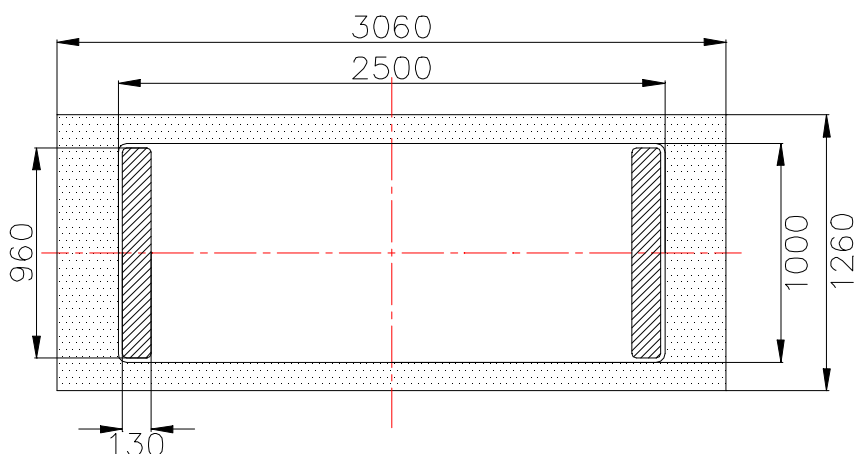


Fig.1 Electrode Pattern and active area